



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

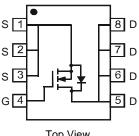
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (approximate)



Top View



Top View Internal Schematic

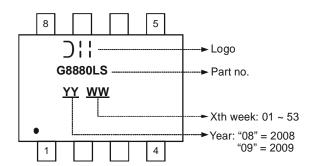
Ordering Information (Note 3)

Part Number	Case	Packaging
DMG8880LSS-13	SO-8	2500 / Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 4)	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	11.6 8.5	Α
Pulsed Drain Current (Note 5)			I _{DM}	80	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	1.43	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 4)	$R_{\theta JA}$	87	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

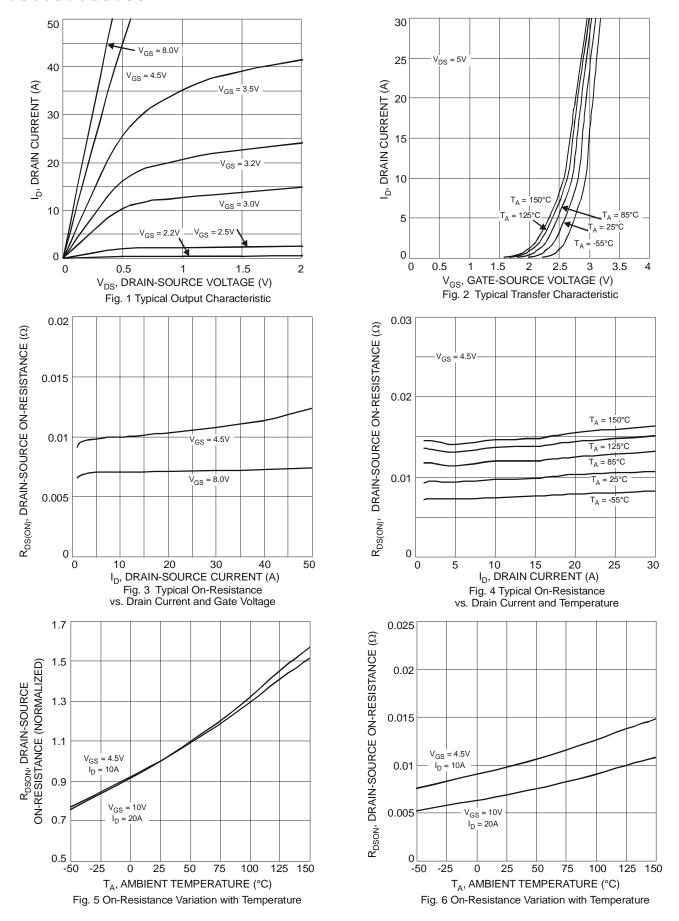
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	1.0	1.5	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	7.0	10	mΩ	$V_{GS} = 10V, I_D = 11.6A$	
Ctatic Brain Course On Resistance	NDS (ON)	-	9.6	14	11122	$V_{GS} = 4.5V, I_D = 10.7A$	
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 2.1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	-	1289	-	pF	4514.14	
Output Capacitance	Coss	-	187	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	162	-	pF	1 = 1.000112	
Gate Resistance	Rg	-	0.97	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge at 10V	Qg	-	27.6	27.6 -	nC	$V_{GS} = 10V, V_{DS} = 15V,$	
Total Gate Gharge at 10V	Qg		27.0			$I_D = 11.6A$, $I_G = 1.0mA$	
Total Gate Charge at 5V	Qg	-	14.4	-	nC	\/ E\/ \/ 4E\/	
Gate-Source Charge	Q_gs	-	3.6	-	nC	$V_{GS} = 5V, V_{DS} = 15V,$	
Gate-Drain Charge	Q_{gd}	-	4.9	-	nC	$I_D = 11.6A, I_G = 1.0mA$	
Turn-On Delay Time	t _{D(on)}	-	7.04	-	ns		
Turn-On Rise Time	t _r	-	17.52	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	-	36.13	-	ns	$R_{GS} = 11\Omega, I_D = 11.6A$	
Turn-Off Fall Time	t _f	-	19.67	-	ns	7	

Notes:

- 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 5. Repetitive rating, pulse width limited by junction temperature.6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.







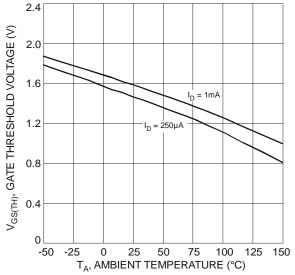
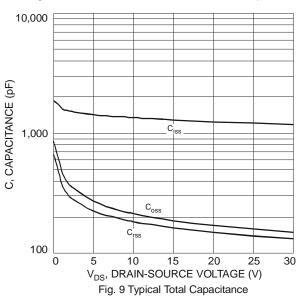
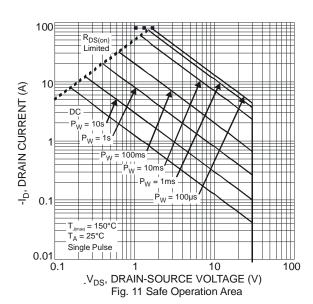
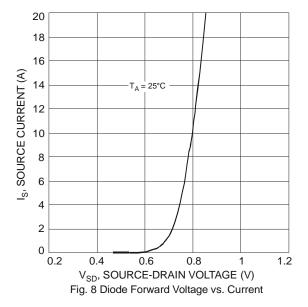
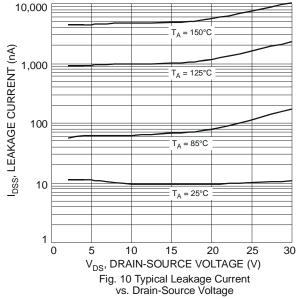


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

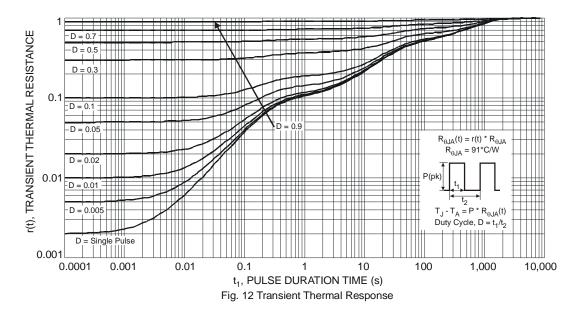




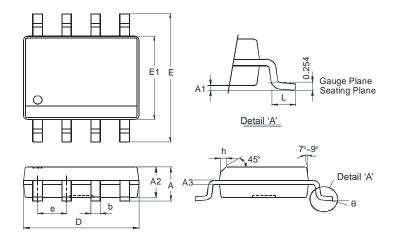






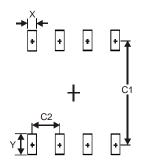


Package Outline Dimensions



SO-8					
Dim	Min	Max			
Α	-	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
А3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	ı	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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